NSN 5961-01-254-2189

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-254-2189 **Inclosure Material:** Metal **Overall Length:** 1.735 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.559 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 nonrepetitive peak reverse voltage and 500.0 repetitive peak reverse voltage and 500.0 repetitive peak off-state voltage **Current Rating Per Characteristic:** 55.00 amperes forward current, average of standard range **Power Rating Per Characteristic:** 20.0 watts small-signal input power, common-collector outside diameter **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Junction pattern arrangement: pnpnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:**